

ABSTRACT OF THE DISCLOSURE

A nitride-based semiconductor light-emitting device capable of improving luminous efficiency by reducing light absorption loss in a contact layer is provided. This
5 nitride-based semiconductor light-emitting device comprises a first conductivity type first nitride-based semiconductor layer formed on a substrate, an active layer, formed on the first nitride-based semiconductor layer, consisting of a nitride-based semiconductor layer, a
10 second conductivity type second nitride-based semiconductor layer formed on the active layer, an undoped contact layer formed on the second nitride-based semiconductor layer and an electrode formed on the undoped contact layer.